



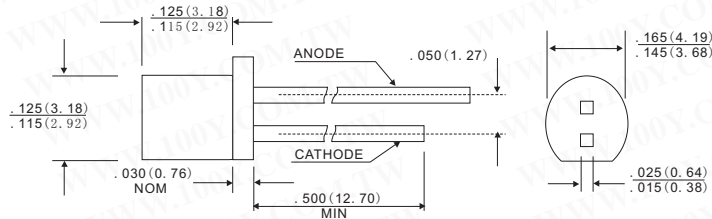
# OPTOELECTRONICS & INDICATORS

the Most Recent Electronic Catalogue 2007

## Infrared Emitting Diode

Detailed product specifications are available on: [us.100y.com.tw](http://us.100y.com.tw)

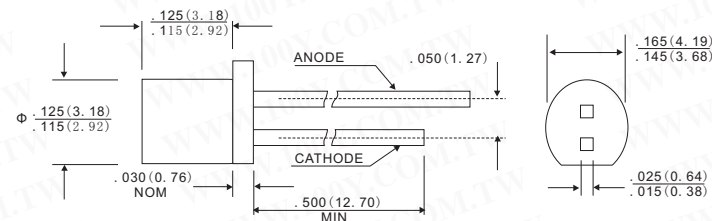
Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36429	OP265B	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1	100mW	890nm	±18 deg	50mA	2V
36430	OP265C	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1	100mW	890nm	±18 deg	50mA	2V
36431	OP265D	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1	100mW	890nm	±18 deg	50mA	2V



### Features

- Wide irradiance pattern
- Mechanically and spectrally matched to the Op505W
- Small package size for space limited applications
- Significantly higher power output than GaAs at equivalent drive currents
- T-1 package style

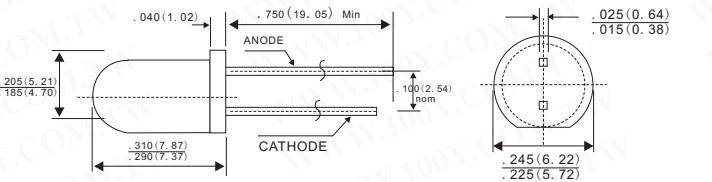
Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36432	OP265W	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1	100mW	890nm	±90deg	50mA	2V



### Features

- Point source irradiance pattern
- Small package size for space limited applications
- T-1 package style

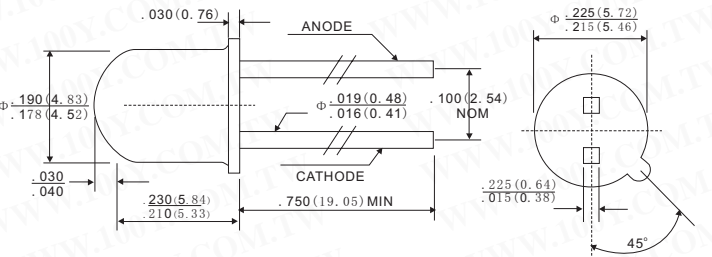
Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36434	OP265WPS	OPTEK	Plastic Point Source In fra red Emitting Diode	T-1	100 mW	850 nm	±60° Deg.	50mA	2V



### FEATURES

- Wide irradiance pattern
- Significantly higher power output than GaAs at equivalent drive currents
- T-1 3/4 package style
- UL recognized, File No. S2047

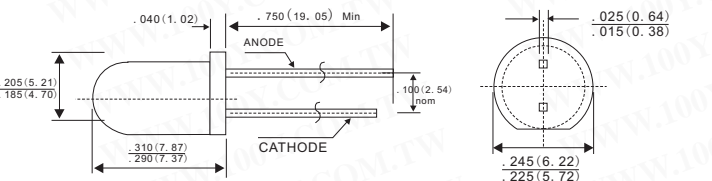
Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
36462	OP290A	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1 3/4	333mW		890nm	±50deg	5A	5V
36463	OP290B	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1 3/4		4V	890	50		
36464	OP290B	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1 3/4	333mW		890nm	±50deg	5A	5V
36465	OP290C	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1 3/4	333mW		890nm	±50deg	5A	5V



### FEATURES

- Wide irradiance pattern (OP293 series)
- Narrow irradiance pattern (OP298 series)
- Mechanically and spectrally matched to the Op593 and Op598 series phototransistors
- Variety of power ranges
- Significantly higher power output than GaAs at equivalent drive currents
- Wavelength matched to silicon's peak response
- Low cost replacement for TO-46 hermetic package.

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36487	OP293A	OPTEK	Infrared Emitting Diode(GaAlAs)	TO-46	142mW	890nm	±60deg	100mA	2V
36488	OP293B	OPTEK	Infrared Emitting Diode(GaAlAs)	TO-46	142mW	890nm	±60deg	100mA	2V
36490	OP293C	OPTEK	Infrared Emitting Diode(GaAlAs)	TO-46	142mW	890nm	±60deg	100mA	2V



### FEATURES

- Narrow irradiance pattern
- Significantly higher power output than GaAs at equivalent drive currents
- T-1 3/4 package style
- UL recognized, File No. S2047
- Wavelength matched to silicon's peak response
- Excellent heat dissipation

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36438	OP295A	OPTEK	Infrared Emitting Diodes(GaAlAs)	T-1 3/4	77mW	890nm	±20deg	5A	5V



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